

200W, 1.8 - 1000 MHz LDMOS Amplifier

Product datasheet

Description

The HTN7G09P200S is an unmatched discrete LDMOS Power Amplifier with 200W saturated output power covering frequency range from 1.8 - 1000 MHz.

Features

Operating Frequency Range: 1.8 - 1000 MHz

Operating Drain Voltage: 20-28V

Saturation Output Power: 200W

• Internally Unmatched device

 Excellent thermal stability due to low thermal resistance package

Enhanced robustness design without device degradation

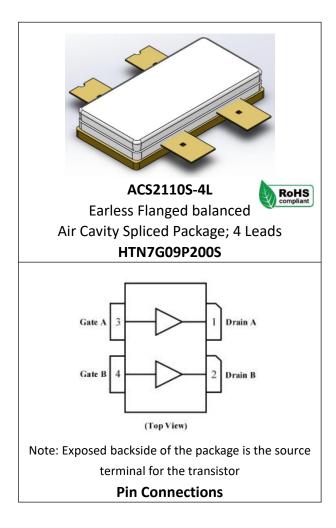
• Internally integrated enhanced ESD design

Applications

- · Analog and Digital Broadcasting
- Meteorological and Aviation Radar
- Private network communication base station
- Industrial Scientific Medical (ISM)
 - Laser generation
 - Plasma generation
 - Particle accelerators
 - MRI, RF ablation and skin treatment
 - Industrial heating, welding and drying systems

Ordering Information

Part Number	Description
HTN7G09P200S	Tray Package
HTN7G09P200S EVB	851 - 880 MHz EVB
HTN7G09P200S EVB1	30 - 678 MHz EVB



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RF Characteristics (Pulsed-CW)

Freq (MHz)	P1dB (dBm)	Eff(%) @P1dB	Gain (dB) @P1dB	P3dB (dBm)	Eff(%) @P3dB
851	53.41	62.33	21.91	54.14	67.05
860	53.14	61.81	21.93	53.75	66.03
869	52.84	62.33	21.86	53.37	66.05
880	52.45	63.89	21.83	52.95	67.71

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ =600mA, PW = 100us, DC= 10% test on WATECH Application Board

RF Characteristics (CW)

Freq (MHz)	P1dB (dBm)	Eff(%) @P1dB	Gain (dB) @P1dB	P3dB (dBm)	Eff(%) @P3dB
851	53.05	59.66	21.80	53.90	64.98
860	52.78	58.94	21.87	53.63	65.31
869	52.67	61.42	21.89	53.35	66.63
880	52.36	63.53	21.87	52.98	68.75

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ =1000mA CW test on WATECH Application Board

RF Characteristics (Pulsed-CW)

Freq (MHz)	P1dB (dBm)	Eff(%) @P1dB	Gain (dB) @P1dB	P3dB (dBm)	Eff(%) @P3dB
30	48.92	46.21	21.40	50.99	59.37
50	49.03	45.76	22.64	51.22	59.06
100	49.49	45.10	20.93	51.82	58.06
200	50.92	49.24	23.24	53.00	60.50
300	50.98	56.37	22.49	52.03	60.73
400	49.79	55.72	21.00	50.65	57.61

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500	50.76	44.98	18.39	51.20	46.04
600	51.90	49.15	19.00	52.48	49.42
678	50.35	48.15	19.48	51.07	48.63

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ = 1200mA, PW = 100us, DC = 10% test on WATECH Application Board

Absolute Maximum Ratings

Parameter	Range/Value	Unit
Drain voltage (VDSS)	-0.5 to +65	V
Gate voltage (V _{GS})	-5 to +10	V
Storage Temperature (Tstg)	-55 to +150	°C
Junction Temperature (T _J)	-40 to +225	°C

Electrical Specification

DC Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Breakdown Voltage V(BR)DSS	Vgs=0V, Ids=108uA	65	-	-	V
Gate-Source Threshold	\/de=\/~a de=100\		1.5		V
Voltage V _{GS(th)}	Vds=Vgs, Ids=108uA	-	1.5	-	V
Drain Leakage Current loss	Vgs=0V, Vds=65V	-	-	10	uA
Gate Leakage Current IGSS	Vgs=5V, Vds=0V	-	-	1	uA

Load Mismatch Test

Condition	Test Result
VSWR=10:1 at all Phase Angles, V_{DD} = +28Vdc, I_{DQ} =600mA, P_{PEAK} = 200W,	No Device
P _{AVG} =20W, PW = 100us, DC= 10%, freq@860MHz	Degradation

Thermal Information

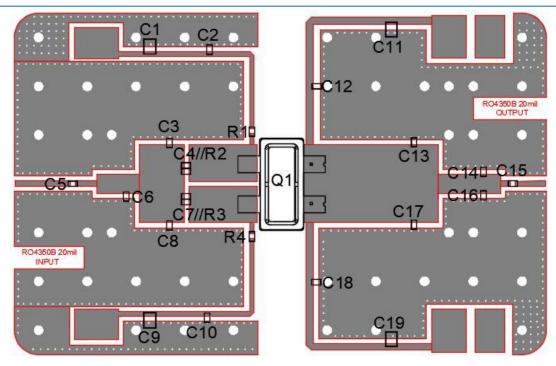
Parameter	Condition	Value (Typ)	Unit
Thermal Resistance	TFLANGE= 80° C, $V_{DD} = +28$ Vdc, $I_{DQ}=600$ mA,	0.4	°C /M
Junction to Case (Rтн)	CW 200W , freq@860MHz	0.4	°C /W



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HTN7G09P200S 851 - 880 MHz Reference Design



EVB Layout

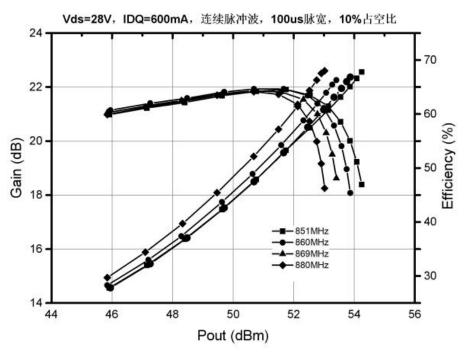
Bill of Materials (BoM) - HTN7G09P200S 851 - 880 MHz Reference Design

Reference	Value	Description	Manufacturer	P/N		
Q1	-	200W, 1.8 - 1000 MHz LDMOS PA	Watech	HTN7G09P200S		
C14,C16	2pF	MLCC	Murata	GQM2195G2E2R0BB12		
C6	2p7F	MLCC	Murata	GQM2195G2E2R7BB12		
C3,C8	5p6F	MLCC	Murata	GQM2195G2E5R6BB12		
C13,C17	7p5F	MLCC	Murata	GQM2195G2E7R5BB12		
C2,C10,C12, C15,C18	24pF	MLCC	Murata	GQM2195C2E240JB12		
C4,C5,C7	5p6F	MLCC	Murata	GQM2195C2E520JB12		
C1,C9,C11,C19	4u7F	MLCC	Murata	GCM32DC72A475KE02L		
R1, R2	10 Ω/0805	Thick Film Resistor	-	-		
R1, R2	4.7 Ω/0805	Thick Film Resistor	-	-		
РСВ	RF35 (er = 3.	RF35 (er = 3.5), 20 mil (0.508 mm), 35 μm (1oz)				

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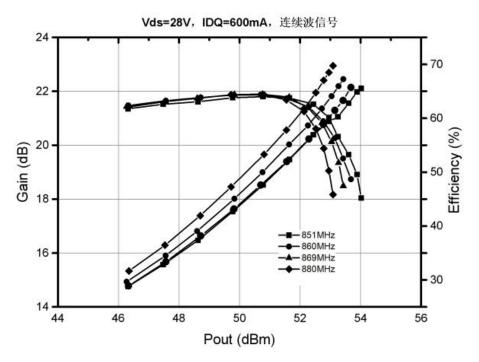
Product datasheet

Performance Plots 851 - 880 MHz



Pulsed CW, Gain and Efficiency vs Pout

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ = 600mA, PW = 100us, DC = 10% test on WATECH Application Board



CW, Gain and Efficiency vs Pout

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ= 600mA test on WATECH Application Board



200W, 1.8 - 1000 MHz LDMOS Amplifier

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HTN7G09P200S 30 - 678 MHz Reference Design



EVB Layout

Bill of Materials (BoM) - HTN7G09P200S

30 - 678 MHz Reference Design

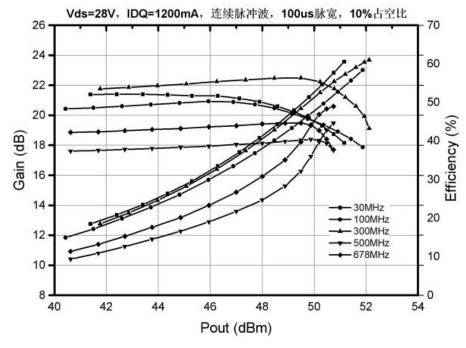
Reference	Value	Description	Manufacturer	P/N
		200W, 1.8 - 1000		
Q1	-	MHz	Watech	HTN7G09P200S
		LDMOS PA		
C1	100pF	MLCC	Murata	GQM2195C2E101JB12D
C2,C3	180pF	MLCC	Murata	GQM2195C2A181GB12D
C5	6p8F	MLCC	Murata	GQM2195G2E6R8BB12
C6	12pF	MLCC	Murata	GQM2195C2E120JB12
C7	15pF	MLCC	Murata	GQM2195C2E150JB12
C4,C8,C9,C11, C12,C14	1nF	MLCC	Murata	GRM3195C2A102JA01D
C10	18pF	MLCC	Murata	GQM2195C2E180JB12
C13	1p2F	MLCC	Murata	GQM2195G2E1R2BB12

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Reference	Value	Description	Manufacturer	P/N
R1, R3, R4	51 Ω/0805	Thick Film Resistor	-	-
R2, R5	10 Ω/0805	Thick Film Resistor	-	-
Coax1	50 Ω SR Coax, 80 mm,2:1		-	-
Coax2,3	16.7 Ω SR Coax, 80 mm,2:1		-	-
Coax4, 5	16.7 Ω SR Coax, 80 mm,2:1		-	-
Coax6	50 Ω SR Coax, 80 mm,2:1		-	-
РСВ	RF35 (er = 3.5), 20 mil (0.508 mm), 35 μm (1oz)			

Performance Plots 30 - 678 MHz



Pulsed CW, Gain and Efficiency vs Pout

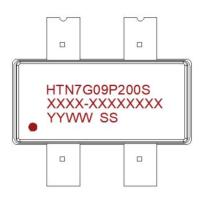
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Package Marking and Dimensions

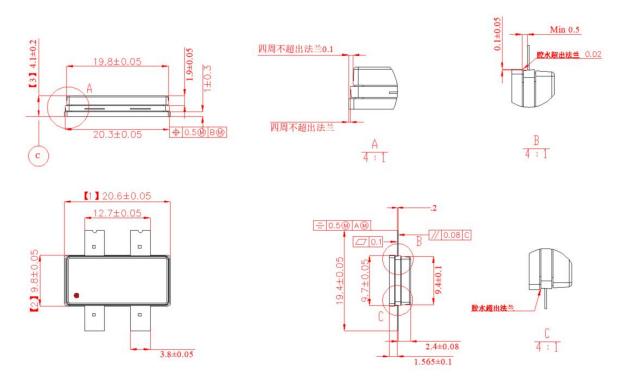


- Line1 (fixed): Device name in W/O
- Line2 (unfixed): Marking Lot No in W/O

(Sample: E596-20140001)

• Line3 (unfixed): Date Code + JY
This Marking SPEC only stipulates
the content of Marking. For
marking requirements such as font
and size, please refer to the latest
version of "Watech Product
Printing Specification"

Marking



Remark: 1.Unit: mm; 2.Unlabeled tolerance is \pm 0.05mm.

Package Dimensions

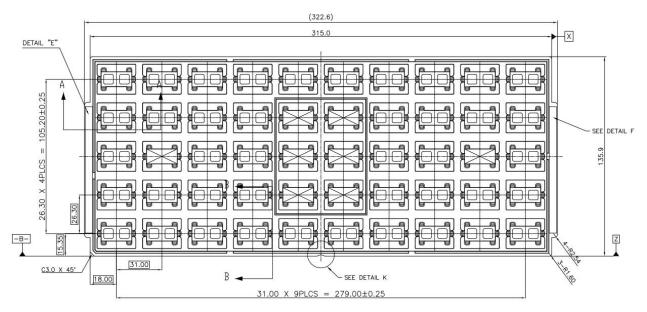
Tape and Reel Information

Package Type	Qty/Tray(pcs)	Qty/Box(pcs)	Qty/Carton(pcs)
ACS2110S-4L	50	300	1800



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Tape & Reel Packaging Descriptions

Handling Precautions

Parameter	Grade
Moisture Sensitivity Level MSL	3

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1B	JESD22-A114
ESD – Human Body Model (MM)	Class A	EIA/JESD22-A115
ESD – Charged Device Model (CDM)	Class III	JESD22-C101



RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

Datasheet Status

Document status	Product status	Definition
Objective Datasheet	Design simulation	Product objective specification
Preliminary Datasheet	Customer sample	Engineering samples and first test results
Product Datasheet	Mass production	Final product specification

WATECH

HTN7G09P200S 200W, 1.8 - 1000 MHz LDMOS Amplifier

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Abbreviations

Acronym	Definition	
LDMOS	Laterally-Diffused Metal-Oxide Semiconductor	
CW	Continuous Waveform	

Revision history

Document ID	Datasheet Status	Release Date	Revision Version
Rev 1.0	Prelimanary	Spet. 2021	Initial Version
Rev 1.1	Product	Oct. 2021	Package Update
Rev 1.2	Product	March 2023	New format based on English version datasheet
Rev 2.0	Product	Oct.2023	Update TBD information
Rev 2.1	Product	March 2024	Version released after re review



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For the latest specifications, additional product information, worldwide sales and distribution locations and information about WATECH:

• Web: <u>www.watechelectronics.com</u>

Email: MKT@huatai-elec.com

For technical questions and application information:

• Email: MKT@huatai-elec.com

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